

N-channel 30 V 9.8 m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 2 — 1 September 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, and QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Load switching

Synchronous buck regulator

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	44	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	34	W
Tj	junction temperature		-55	-	175	°C
Static char	racteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_{D} = 15 \text{ A};$ $T_{j} = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 12}}{}$	-	10.3	12.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_i = 25 \text{ °C}; \text{ see Figure 12}$	-	8.3	9.8	mΩ



N-channel 30 V 9.8 mΩ logic level MOSFET in LFPAK using NextPower technology

Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic ch	naracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A};$ $V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15};$ see $\frac{\text{Figure } 15}{\text{Figure } 15}$	-	1.6	-	nC
Q _{G(tot)}	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A};$ $V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15};$ see $\frac{\text{Figure } 15}{\text{Figure } 15}$	-	5	-	nC

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S S

SOT669 (LFPAK; Power-SO8)

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PSMN9R5-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	30	V
V_{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 k Ω	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{M}}$	-	44	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	-	31	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 4	-	177	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	34	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	150	-	V
Source-drain	n diode				
Is	source current	T _{mb} = 25 °C	-	31	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	177	Α
Avalanche ru	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 44 A; $V_{sup} \le 30$ V; R_{GS} = 50 Ω; unclamped; see Figure 3	-	9	mJ

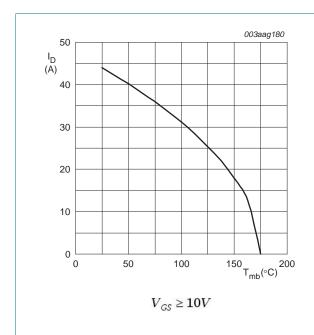
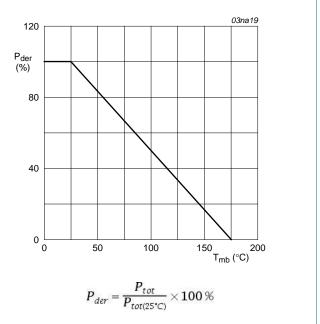
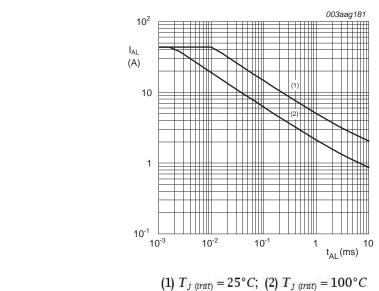


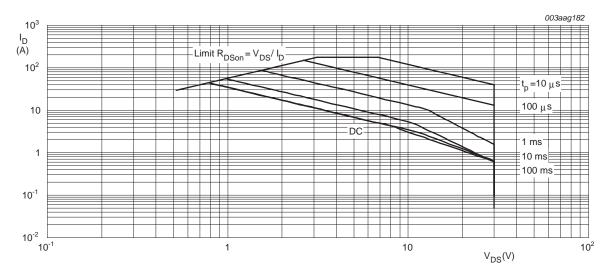
Fig 1. Continuous drain current as a function of mounting base temperature



g 2. Normalized total power dissipation as a function of mounting base temperature



Single pulse avalanche rating; avalanche current as a function of avalanche time Fig 3.



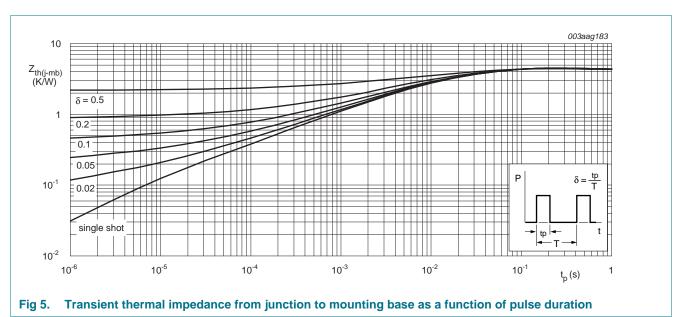
 $T_{mb} = 25$ °C; I_{DM} is a single pulse

Safe operating area; continuous and peak drain currents as a function of drain-source voltage Fig 4.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 5	-	4.14	4.36	K/W



6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
_	racteristics			7 F		
V _{(BR)DSS}	drain-source breakdown	I _D = 250 μA; V _{GS} = 0 V; T _i = 25 °C	30	-	-	V
(511)500	voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 V; T_i = -55 ^{\circ}\text{C}$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	, , , , , , , , , , , , , , , , , , ,	1.05	1.66	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_i = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μA
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	10.3	12.1	mΩ
	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	-	20.3	mΩ	
	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	8.3	9.8	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 150 \text{ °C};$ see Figure 12; see Figure 13	-	-	16.5	mΩ
R _G	gate resistance	f = 1 MHz	-	2.35	4.7	Ω
Dynamic o	characteristics					
Q _{G(tot)} total gate charge	I_D = 15 A; V_{DS} = 15 V; V_{GS} = 10 V; see Figure 14; see Figure 15	-	10.4	-	nC	
		I _D = 15 A; V _{DS} = 15 V; V _{GS} = 4.5 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	5	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	10.1	-	nC
Q_{GS}	gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	1.6	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	1.1	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	0.5	-	nC
Q_{GD}	gate-drain charge		-	1.6	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 15 \text{ A}$; $V_{DS} = 15 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.77	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	681	-	рF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	169	-	pF
C _{rss}	reverse transfer capacitance		-	50	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 1 \Omega; V_{GS} = 4.5 \text{ V};$	-	13	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	8.8	-	ns
t _{d(off)}	turn-off delay time		-	15	-	ns
t _f	fall time		-	4.7	-	ns

 Table 6.
 Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	4.4	-	nC	
Source-drain	Source-drain diode						
V _{SD}	source-drain voltage	$I_S = 15 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.86	1.1	V	
t _{rr}	reverse recovery time	$I_S = 15 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	10	-	ns	
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	18	-	nC	
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V}; I_S = 15 \text{ A};$	-	11	-	ns	
t _b	reverse recovery fall time	$dl_S/dt = -100 A/\mu s$; $V_{DS} = 15 V$; see Figure 18	-	7	-	ns	

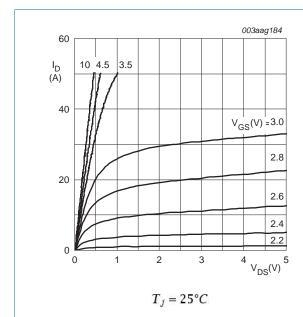
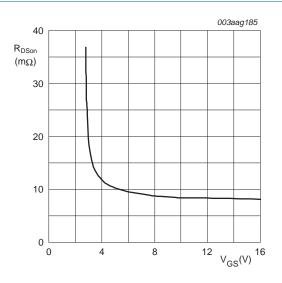


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



 $T_j=25^{\circ}C;\ I_D=15A$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

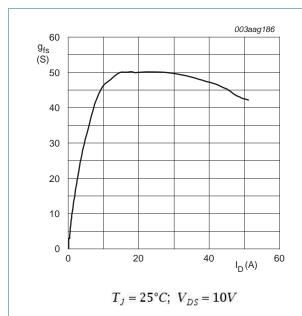
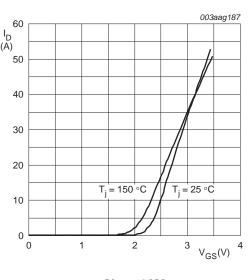


Fig 8. Forward transconductance as a function of drain current; typical values



 $V_{DS} = 10V$

Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

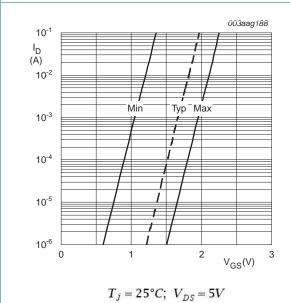


Fig 10. Sub-threshold drain current as a function of gate-source voltage

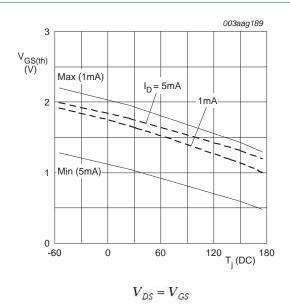


Fig 11. Gate-source threshold voltage as a function of junction temperature

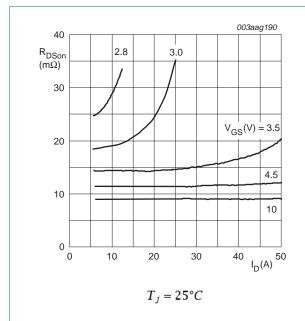


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

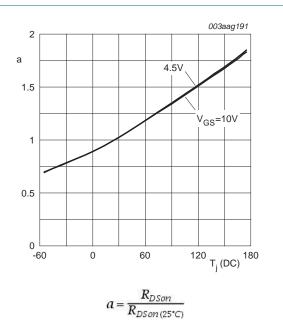


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

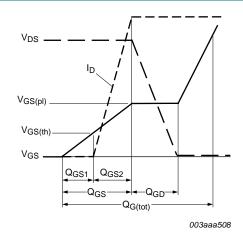
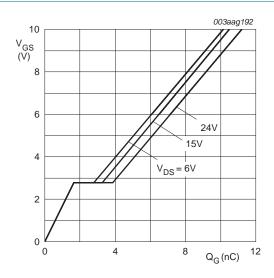


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; \ I_D = 15A$

Fig 15. Gate-source voltage as a function of gate charge; typical values

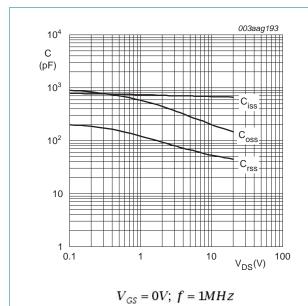


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

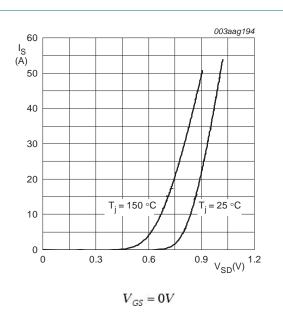


Fig 17. Source current as a function of source-drain voltage; typical values

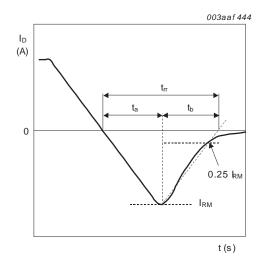
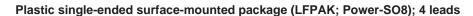
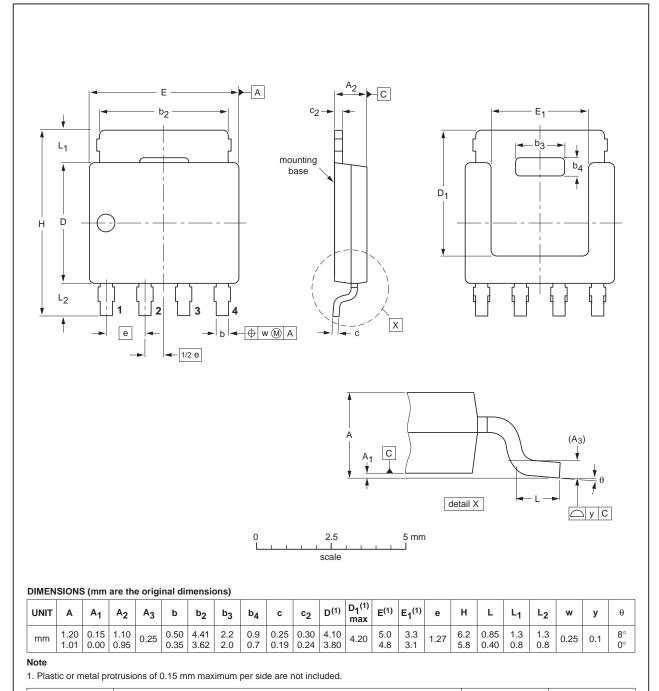


Fig 18. Reverse recovery timing definition

7. Package outline



SOT669



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT669		MO-235				-06-03-16- 11-03-25

Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN9R5-30YLC

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N-channel 30 V 9.8 mΩ logic level MOSFET in LFPAK using NextPower technology

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN9R5-30YLC v.2	20110901	Product data sheet	-	PSMN9R5-30YLC v.1
Modifications:	 Status changed from 	m preliminary to product.		
	 Various changes to 	content.		
PSMN9R5-30YLC v.1	20110711	Preliminary data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PSMN9R5-30YLC

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